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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

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Keep safety first in your circuit designs!

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Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

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HVC145

Silicon Epitaxial Planar Pin Diode for High Frequency Switching



ADE-208-1500B (Z)

Rev.2
Jun. 2002

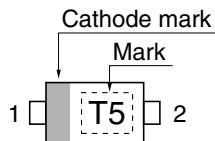
Features

- Low capacitance. ($C = 0.45 \text{ pF max}$)
- Low forward resistance. ($r_f = 1.8 \Omega \text{ max}$)
- Ultra small Flat Package (UFP) is suitable for surface mount design.

Ordering Information

Type No.	Laser Mark	Package Code
HVC145	T5	UFP

Pin Arrangement



1. Cathode
2. Anode

Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Value	Unit
Reverse voltage	V_R	60	V
Forward current	I_F	50	mA
Power dissipation	Pd	150	mW
Junction temperature	Tj	125	°C
Storage temperature	Tstg	-55 to +125	°C

Electrical Characteristics

(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse current	I_R	—	—	100	nA	$V_R = 60$ V
Forward voltage	V_F	—	—	0.9	V	$I_F = 2$ mA
Capacitance	C	—	—	0.45	pF	$V_R = 1$ V, $f = 1$ MHz
Forward resistance	r_f	—	—	1.8	Ω	$I_F = 10$ mA, $f = 100$ MHz
ESD-Capability ^{*1}	—	100	—	—	V	C = 200 pF, R = 0 Ω , Both forward and reverse direction 1 pulse.

Note: 1. Failure criterion ; $I_R \geq 100$ nA at $V_R = 60$ V

Main Characteristic

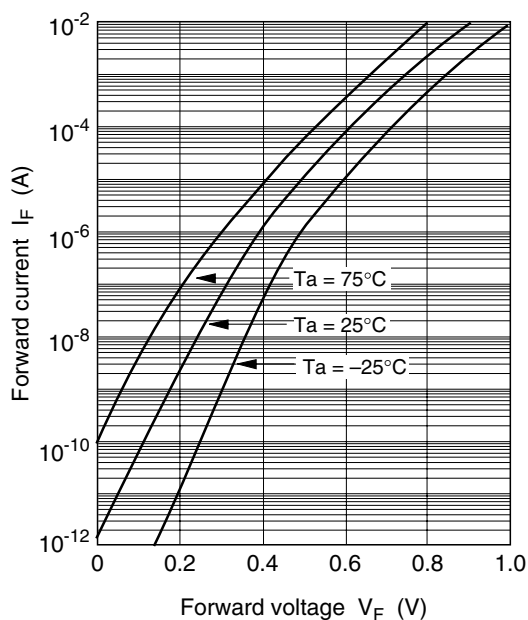


Fig.1 Forward current vs. Forward voltage

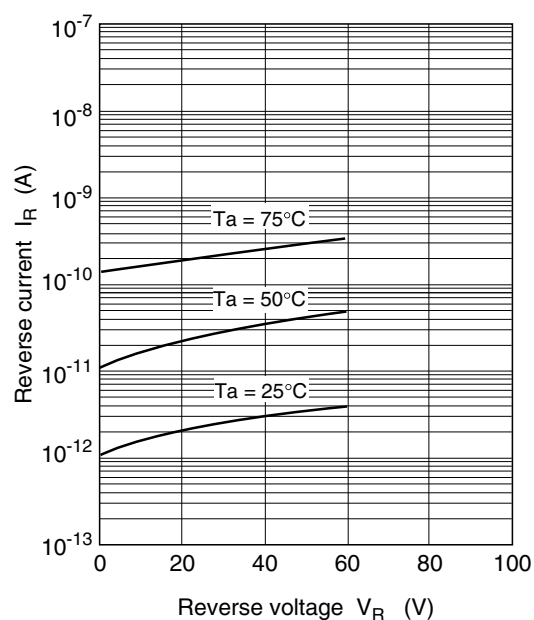


Fig.2 Reverse current vs. Reverse voltage

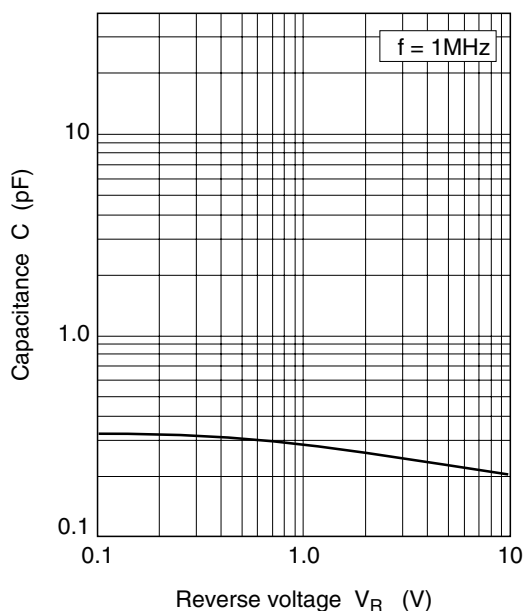


Fig.3 Capacitance vs. Reverse voltage

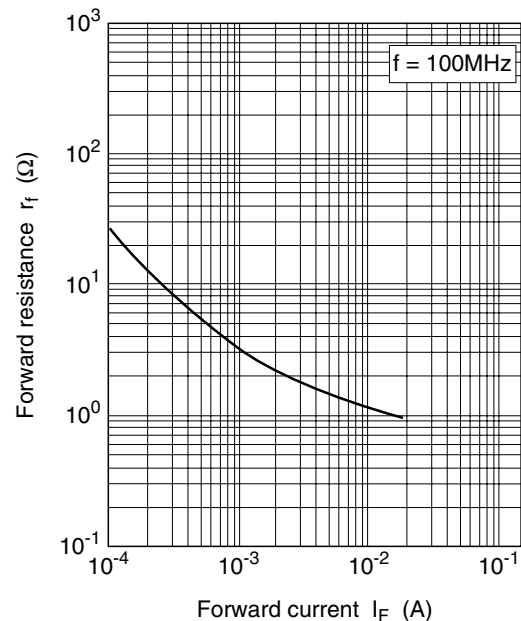


Fig.4 Forward resistance vs. Forward current

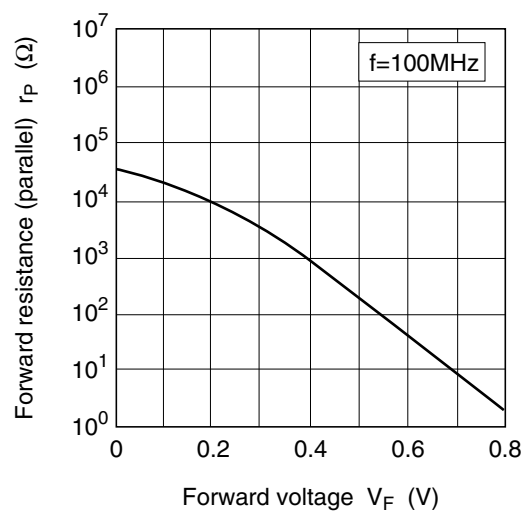
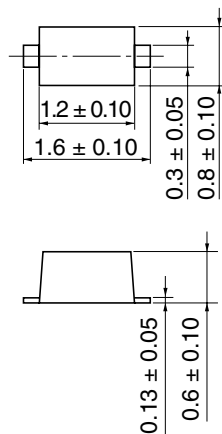


Fig.5 Forward resistance (parallel) vs. Forward voltage

Package Dimensions

As of January, 2002

Unit: mm



Hitachi Code	UFP
JEDEC	—
JEITA	Conforms
Mass (reference value)	0.0016 g

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Sales Offices**HITACHI****Hitachi, Ltd.**

Semiconductor & Integrated Circuits
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
Tel: (03) 3270-2111 Fax: (03) 3270-5109

URL <http://www.hitachisemiconductor.com/>

For further information write to:

Hitachi Semiconductor (America) Inc.
179 East Tasman Drive
San Jose, CA 95134
Tel: <1> (408) 433-1990
Fax: <1> (408) 433-0223

Hitachi Europe Ltd.
Electronic Components Group
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA, United Kingdom
Tel: <44> (1628) 585000
Fax: <44> (1628) 585200

Hitachi Europe GmbH
Electronic Components Group
Dornacher Straße 3
D-85622 Feldkirchen
Postfach 201, D-85619 Feldkirchen
Germany
Tel: <49> (89) 9 9180-0
Fax: <49> (89) 9 29 30 00

Hitachi Asia Ltd.
Hitachi Tower
16 Collyer Quay #20-00
Singapore 049318
Tel: <65>-6538-6533/6538-8577
Fax: <65>-6538-6933/6538-3877
URL: <http://semiconductor.hitachi.com.sg>

Hitachi Asia Ltd.
(Taipei Branch Office)
4/F, No. 167, Tun Hwa North Road
Hung-Kuo Building
Taipei (105), Taiwan
Tel: <886>-(2)-2718-3666
Fax: <886>-(2)-2718-8180
Telex: 23222 HAS-TP
URL: <http://www.hitachi.com.tw>

Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower
World Finance Centre,
Harbour City, Canton Road
Tsim Sha Tsui, Kowloon Hong Kong
Tel: <852>-2735-9218
Fax: <852>-2730-0281
URL: <http://semiconductor.hitachi.com.hk>

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